

**IN THE CLAIMS**

*Please amend the claims as follows:*

1. (Currently Amended) A semiconductor laser device, comprising:  
a semiconductor laser element arranged inside an airtight-sealed package, the semiconductor laser element having an active region formed of a gallium nitride-based crystal, wherein a rated output power of the semiconductor laser device is 30 mW or more, and an atmospheric gas inside the package is a mixture gas containing oxygen and hydrogen nitrogen, with an oxygen content of more than 20%, and the semiconductor laser device has a MTTF of 3,000 hours or more at 70°C.
2. (Original) The semiconductor laser device of claim 1, wherein the semiconductor laser element has a dielectric oxide film formed on a laser emission surface thereof.
3. (Cancelled)
4. (Original) The semiconductor laser device of claim 1, wherein the semiconductor laser element emits light having a wavelength of 0.9  $\mu\text{m}$  or less.
5. (Previously Presented) The semiconductor laser device of claim 1, wherein the atmospheric gas inside the package is dry air.
- 6-8. (Cancelled)

9. (Previously Presented) The semiconductor laser device of claim 1, wherein the gallium nitride-based crystal is an AlGaN- or InGaN-based crystal.